

AMENDMENTS TO THE CLAIMS

Please amend the claims as shown below. A complete listing of all pending claims is presented.

1. (Previously Presented) A semiconductor device comprising:

a semiconductor mesa portion formed on a substrate, including a stack of at least a collector layer, a base layer, and an emitter layer formed in narrower region compared with said base layer, and functioning as an active region of a bipolar transistor;

a base contact pad mesa portion formed on said substrate apart from said semiconductor mesa portion and formed with a height the same as the height of the top surface of said base layer; and

a conductive layer formed integrally with a base electrode formed connected to said base layer at part of a region of formation of said base layer other than the region of formation of said emitter layer, a base contact pad electrode formed above said base contact pad mesa portion in a region other than near the edges of the top surface of said base contact pad mesa portion, and an interconnect for connecting said base electrode and said base contact pad electrode, wherein an insulating film is formed below said conductive layer between said semiconductor mesa portion and said base contact pad mesa portion.

2. (Original) A semiconductor device as set forth in claim 1, wherein the surface layer of said base contact pad mesa portion is formed by the same layer as said base layer.

3. (Original) A semiconductor device as set forth in claim 1, wherein the area under said conductive layer between said semiconductor mesa portion and said base contact pad mesa portion forms a space.

4. (Canceled)

5. (Original) A semiconductor device as set forth in claim 1, wherein said base electrode is formed in a region other than the region of formation of said emitter layer and other than near the edges of said base layer.

6. (Original) A semiconductor device as set forth in claim 1, wherein a distance between said semiconductor mesa portion and said base contact pad mesa portion is 1 to 5 μm .

7. (Original) A semiconductor device as set forth in claim 1, wherein said semiconductor mesa portion is comprised of a stack of a compound semiconductor and has a heterojunction bipolar transistor.

8. (Cancelled)

9. (Cancelled)

10. (Cancelled)

11. (Cancelled)

12. (Cancelled)

13. (New) A semiconductor device comprising:

a semiconductor mesa portion formed on a substrate, including a stack of at least a collector layer, a base layer, and an emitter layer formed in narrower region compared with said base layer, and functioning as an active region of a bipolar transistor;

a base contact pad mesa portion formed on said substrate apart from said semiconductor mesa portion and formed with a height the same as the height of the top surface of said base layer; and

a conductive layer formed integrally with a base electrode formed connected to said base layer at part of a region of formation of said base layer other than the region of formation of said emitter layer, a base contact pad electrode formed above said base contact pad mesa portion in a region other than near the edges of the top surface of said base contact pad mesa portion, and an interconnect for connecting said base electrode and said base contact pad electrode, wherein said base electrode is formed in a region other than the region of formation of said emitter layer and other than near the edges of said base layer.

14. (New) A semiconductor device as set forth in claim 13, wherein the surface layer of said base contact pad mesa portion is formed by the same layer as said base layer.

15. (New) A semiconductor device as set forth in claim 13, wherein the area under said conductive layer between said semiconductor mesa portion and said base contact pad mesa portion forms a space.

16. (New) A semiconductor device as set forth in claim 13, wherein a distance between said semiconductor mesa portion and said base contact pad mesa portion is 1 to 5 μm .

17. (New) A semiconductor device as set forth in claim 13, wherein said semiconductor mesa portion is comprised of a stack of a compound semiconductor and has a heterojunction bipolar transistor.